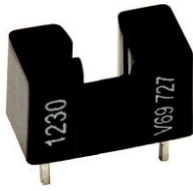
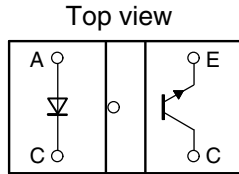


Transmissive Optical Sensor with Phototransistor Output



21833



19205_1

DESCRIPTION

The TCST1230 is a transmissive sensor that includes an infrared emitter and phototransistor, located face-to-face on the optical axes in a leaded package which blocks visible light.

FEATURES

- Package type: leaded
- Detector type: phototransistor
- Dimensions (L x W x H in mm): 9.2 x 4.8 x 5.4
- Gap (in mm): 2.8
- Aperture (in mm): 0.5
- Typical output current under test: $I_C = 2$ mA
- Daylight blocking filter
- Emitter wavelength: 950 nm
- Lead (Pb)-free soldering released
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

APPLICATIONS

- Optical switch
- Shaft encoder
- Detection of opaque material such as paper
- Detection of magnetic tapes

PRODUCT SUMMARY

PART NUMBER	GAP WIDTH (mm)	APERTURE WIDTH (mm)	TYPICAL OUTPUT CURRENT UNDER TEST ⁽¹⁾ (mA)	DAYLIGHT BLOCKING FILTER INTEGRATED
TCST1230	2.8	0.5	2	Yes

Note

- Conditions like in table basic characteristics/coupler

ORDERING INFORMATION

ORDERING CODE	PACKAGING	VOLUME ⁽¹⁾	REMARKS
TCST1230	Tube	MOQ: 4800 pcs, 60 pcs/tube	-

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25$ °C, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
COUPLER				
Total power dissipation	$T_{amb} \leq 25$ °C	P_{tot}	250	mW
Ambient temperature range		T_{amb}	- 25 to + 85	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	Distance to package 1.6 mm, $t \leq 5$ s	T_{sd}	260	°C
INPUT (EMITTER)				
Reverse voltage		V_R	6	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10$ μ s	I_{FSM}	3	A
Power dissipation	$T_{amb} \leq 25$ °C	P_V	100	mW
Junction temperature		T_j	100	°C

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
OUTPUT (DETECTOR)				
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	100	mA
Power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	P_V	150	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$

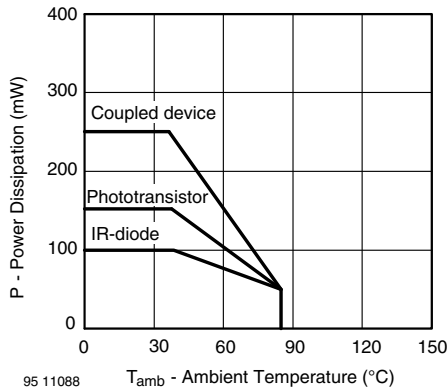
ABSOLUTE MAXIMUM RATINGS


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
COUPLER						
Collector current	$V_{CE} = 10\text{ V}$, $I_F = 20\text{ mA}$	I_C	0.5		14	mA
Collector emitter saturation voltage	$I_F = 20\text{ mA}$, $I_C = 0.2\text{ mA}$	V_{CEsat}			0.4	V
INPUT (EMITTER)						
Forward voltage	$I_F = 60\text{ mA}$	V_F		1.25	1.5	V
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_j		50		pF
OUTPUT (DETECTOR)						
Collector emitter voltage	$I_C = 1\text{ mA}$	V_{CEO}	70			V
Emitter collector voltage	$I_E = 10\text{ }\mu\text{A}$	V_{ECO}	7			V
Collector dark current	$V_{CE} = 25\text{ V}$, $I_F = 0\text{ A}$, $E = 0\text{ lx}$	I_{CEO}		10	100	nA
SWITCHING CHARACTERISTICS						
Turn-on time	$I_C = 1\text{ mA}$, $V_{CE} = 5\text{ V}$, $R_L = 100\text{ }\Omega$ (see figure 2)	t_{on}		15		μs
Turn-off time	$I_C = 1\text{ mA}$, $V_{CE} = 5\text{ V}$, $R_L = 100\text{ }\Omega$ (see figure 2)	t_{off}		10		μs